

Lateral confinement of cylindrical domain thin polymer films

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What is a polymer?

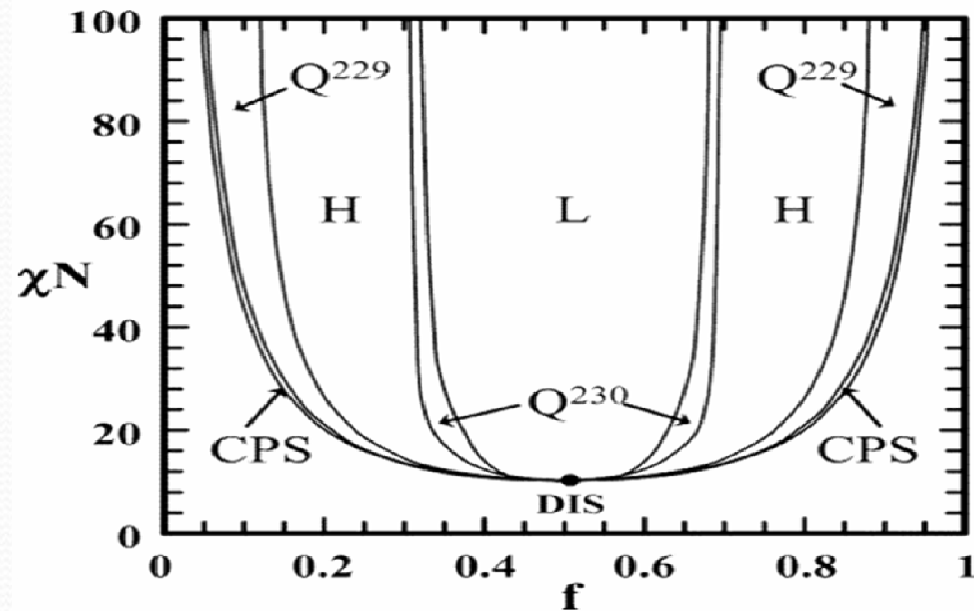
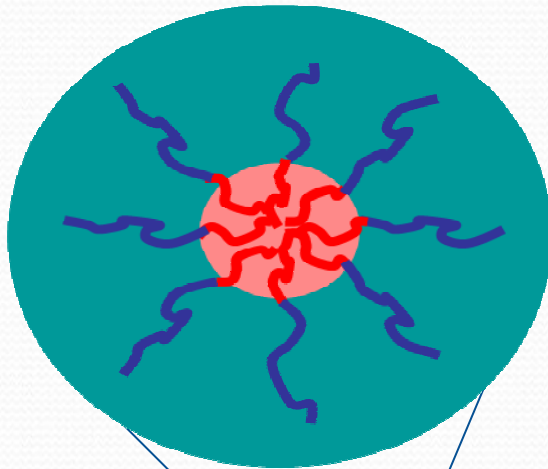
- Repeated structural units linked by covalent bonds
- Block copolymers
 - Two polymer chains linked by a covalent bond



Poly (styrene-b-vinyl pyridine)

Block copolymer phase behavior

Cross-sectional view



S

C

G

L

G'

C'

S'

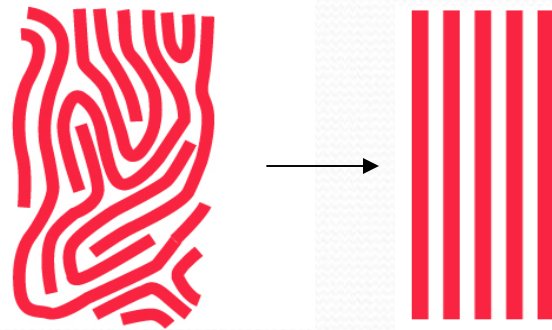
f_A

Why study this system?

- Nanolithography: alternate method for creating masks with nanofeatures
- Current methods: photolithography, e-beam lithography
 - Can't create structures smaller than wavelength (λ) of light
 - Ultraviolet and X-rays possible, but still expensive
- Obtain even smaller features
- Nanowires
- Etch away the PVP to leave nanocylindrical holes behind
- Fill with metallic salt to make nanowires

What do we hope to accomplish?

- The block copolymer Poly (styrene-*b*-2-vinyl pyridine), or PS-PVP, self-assembles into a cylindrical array
 - 25% PVP : volume ratio
- Pattern is disordered
- We aim to improve translational and orientational order by graphoepitaxy
 - Using substrate to direct growth of overlying material



Disordered system

Ordered system

Experimental Method

- Film casting
- Annealing
- Imaging
 - Secondary Ion Mass Spectrometry (SIMS)
 - Atomic Force Microscopy (AFM)

Preparation of ordered films

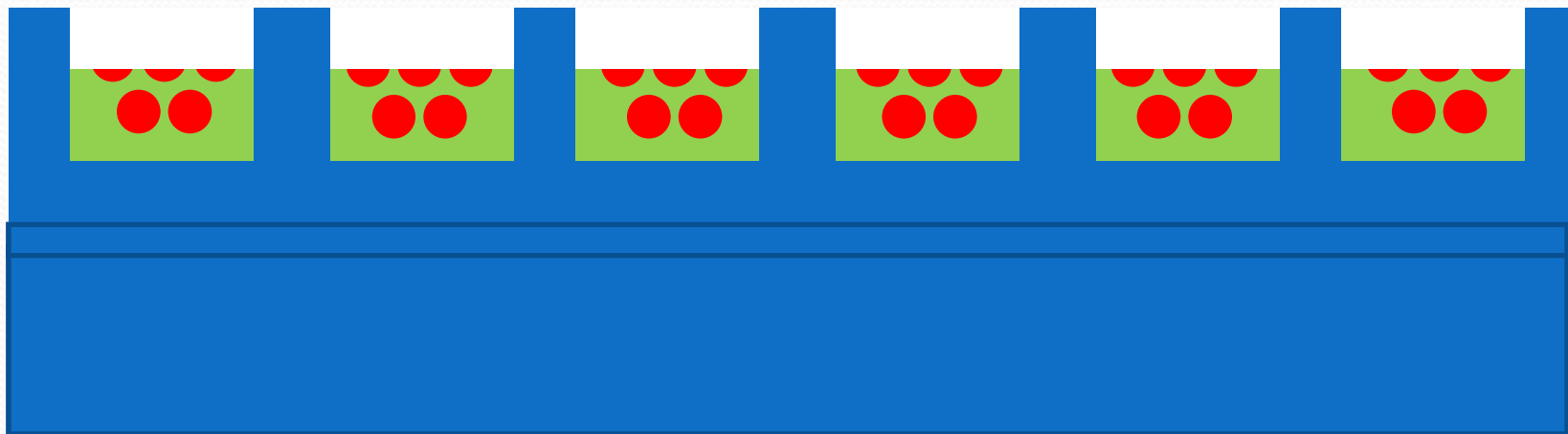
- Dissolve polymer in toluene
 - 2% mass solution
- Spin coat on a silicon (Si) wafer at a specific rpm for 45 seconds
 - Thickness is inversely proportional to spin speed
 - We are targeting films of a specific thickness

Annealing

- Heat beyond the Order-Disorder Temperature (ODT)
 - ODT for PS-PVP is $\sim 220^{\circ}\text{C}$
- Cool down to the annealing temperature
 - Range of annealing temp. (AT) is $\sim 150\text{-}200^{\circ}\text{C}$
 - We hold it at the AT for 2 days

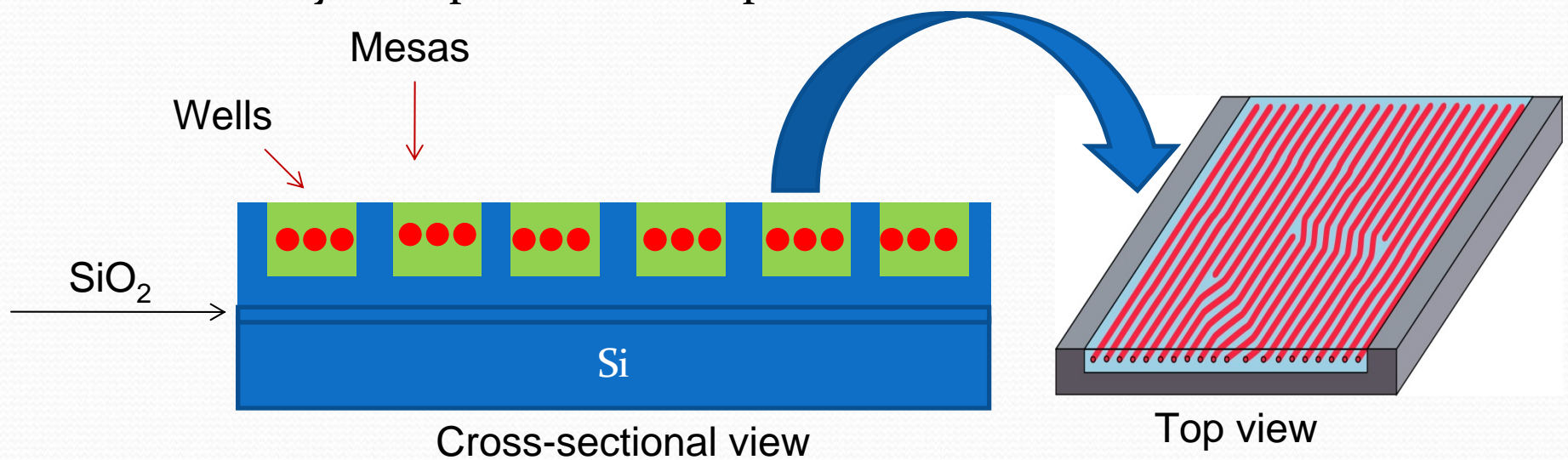
Accessing the 'buried structure'

- Secondary Ion Mass Spectrometry (SIMS) to etch through PS film
 - Process exposes cylinders
- Analyze cylinder patterns using Atomic Force Microscopy (AFM)

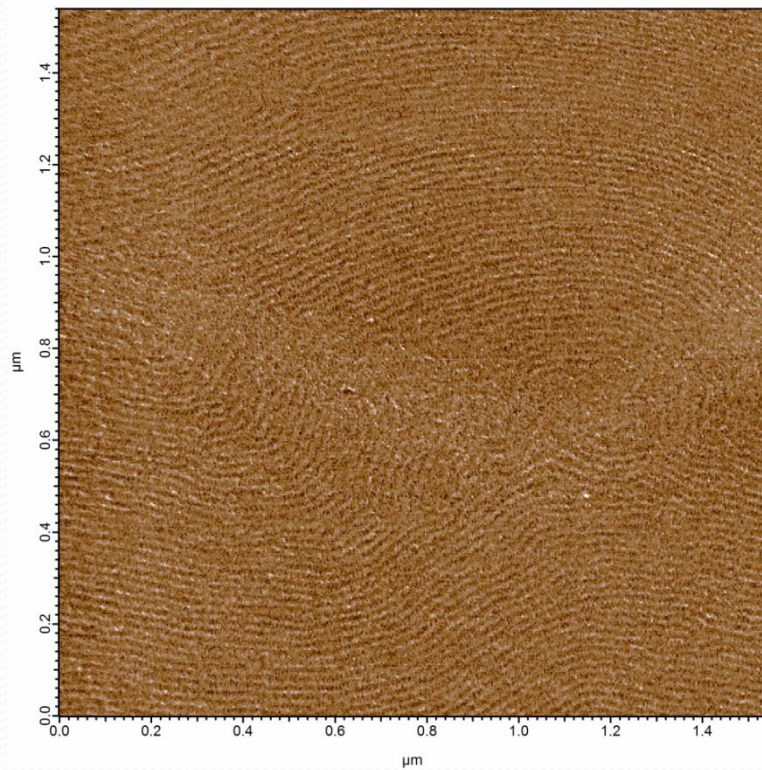


Data collection

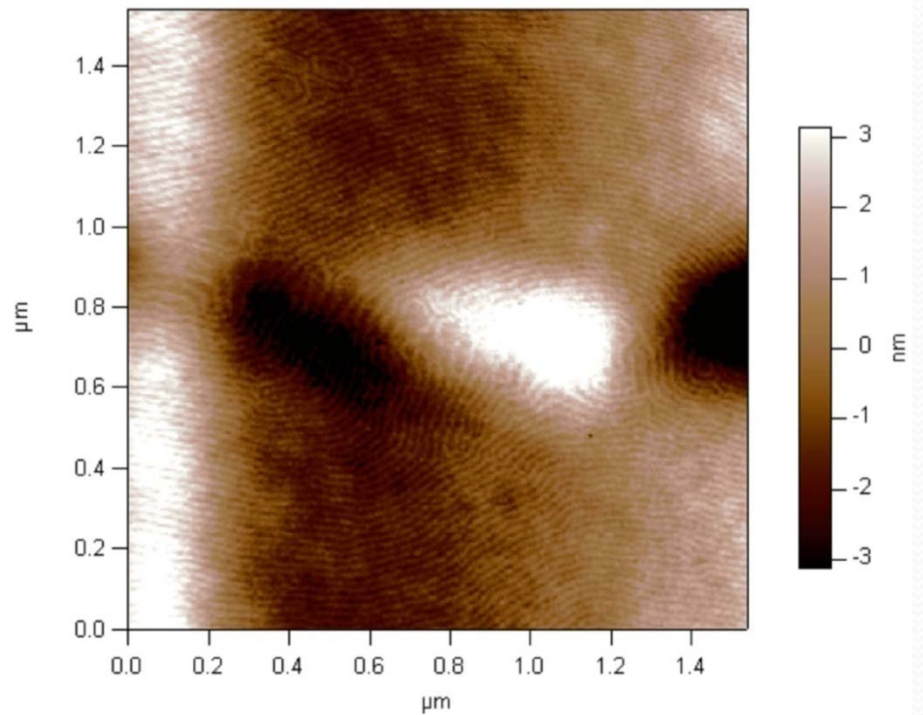
- We looked at two different kinds of films
 - Unconfined films
 - Polymer spun coat on a plain Si wafer
 - Confined films
 - Polymer spun coat on a patterned wafer



Disordered System (Plain Si wafer)

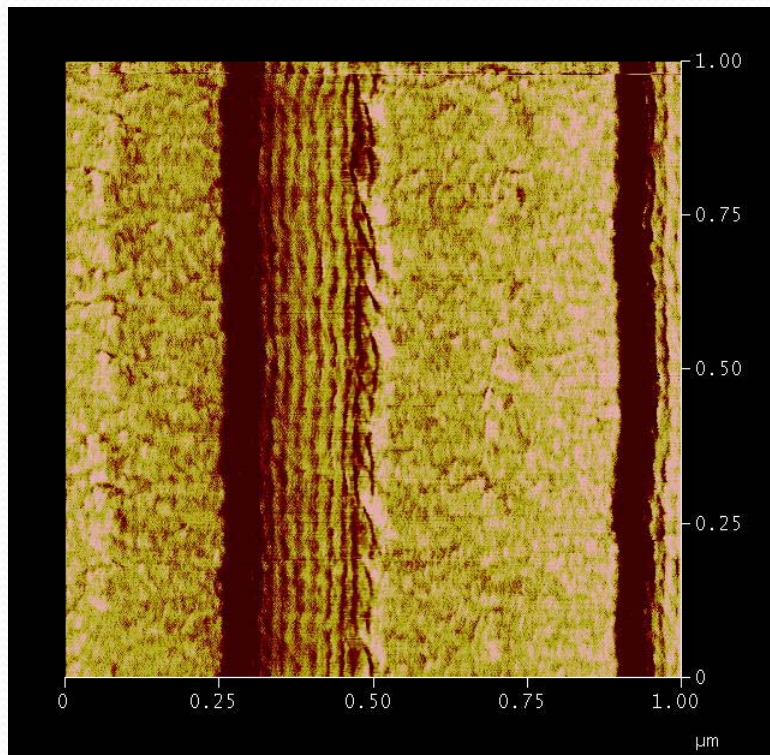


AFM Phase Scan



AFM Height Scan

Confined system (patterned wafer)

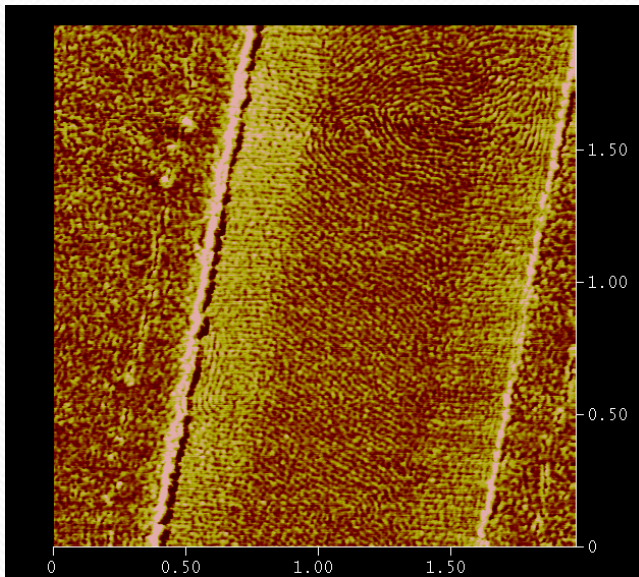


AFM Height Scan

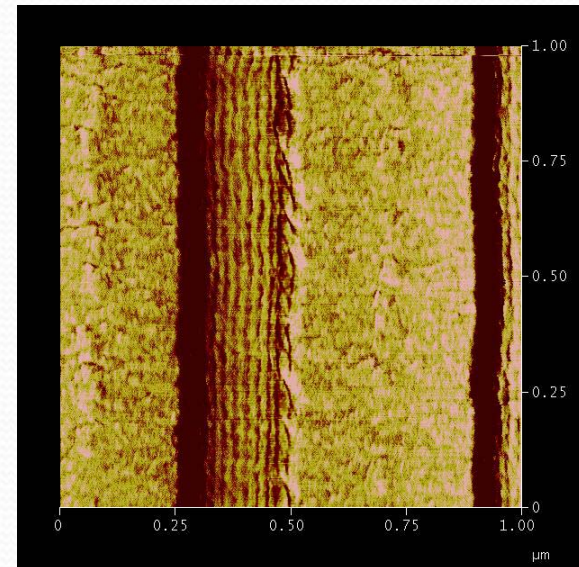


AFM Phase Scan

Comparison of width



Width of channel ~ 1.36 μm

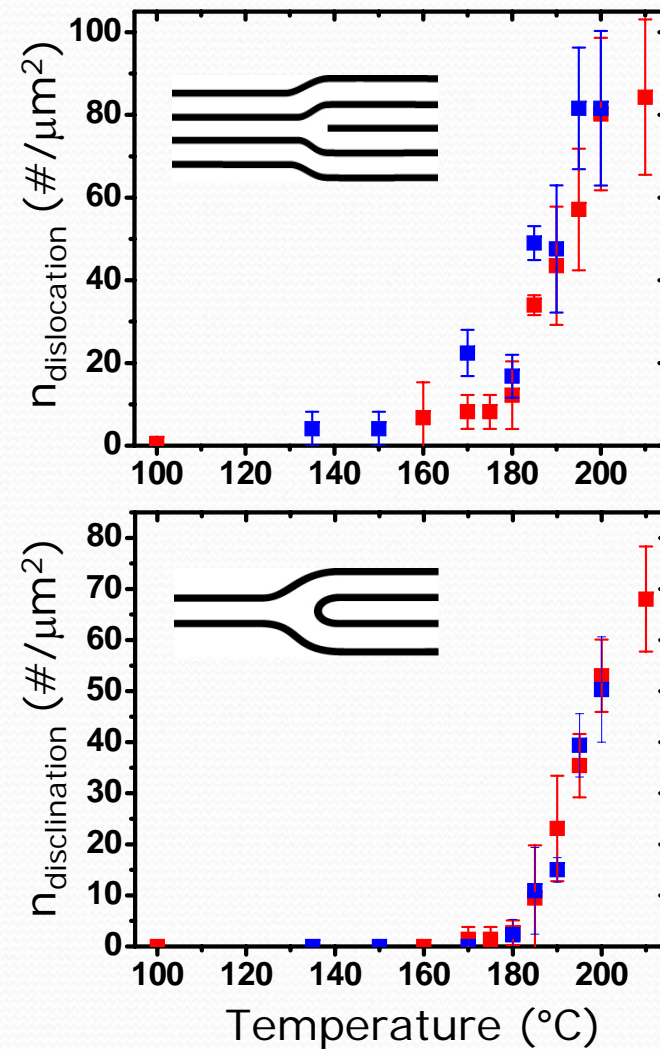


Width of channel ~ 0.23 μm

Monolayer Defect Densities

Defects

- For monolayer, dislocation density is low but nonzero
- Disclination density is zero



Graphs courtesy of M. R. Hammond: *In-Plane Microdomain Order in Cylindrical Block Copolymer Thin Films*, 2005, *Macromolecules*

Summary

- Accomplishments
 - Learned about block copolymers
 - Improved translational and orientational order of cylinders
 - Learned how to operate AFM
 - Use existing methods to create smaller structures
 - Save \$\$\$\$\$\$

Future plans

- Quantification of defect density
- Compare the effects of channel walls to an unconstrained system
- Determine the effects of channel width and temperature
- Find the cause of defects



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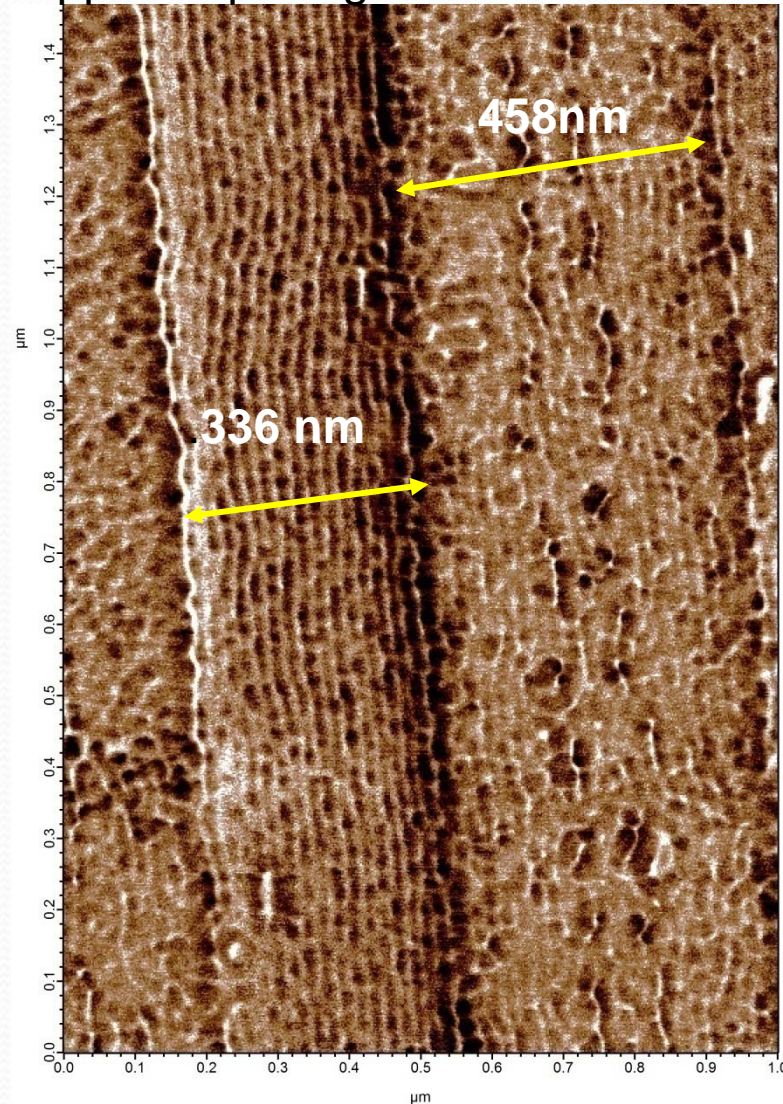
CNSI, NSF, IBM

Block Copolymers



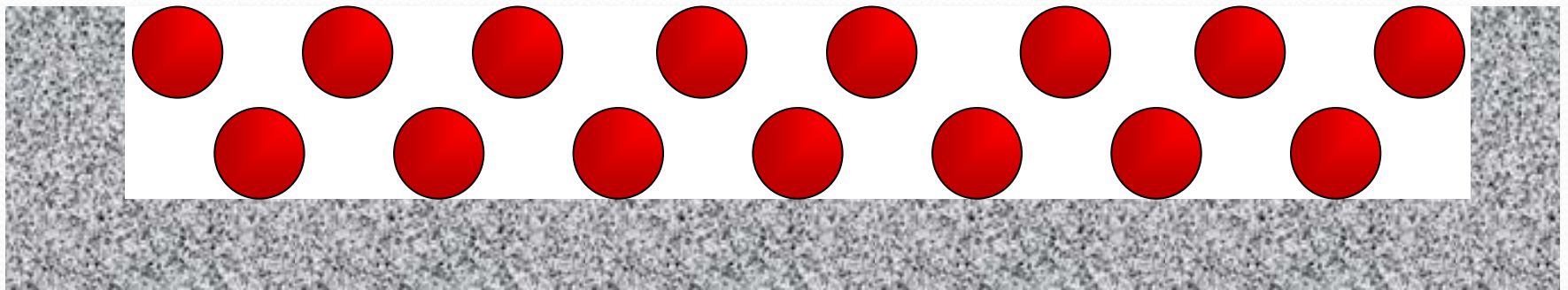
AFM Phase Image

Approx. width of cylinder = 9.08 nm
Approx. spacing = 11.3 nm

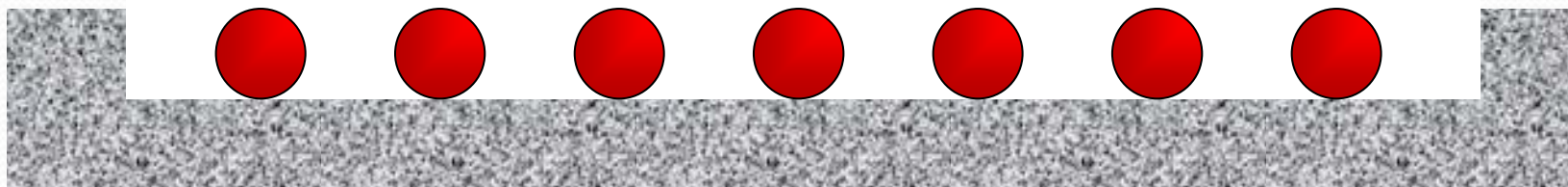



Patterned Si wafer

Bilayers



Monolayer



- 
- Top-down
 - Start w/bulk and remove unwanted material
 - Destructive procedure
 - Bottom-up
 - Start from a scale smaller than desired feature size (e.g. molecular level to create nanofeatures)
 - Build up from that
 - Spontaneous building up = self-assembly
 - Thermodynamically favored